Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6,486,037".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 15:41
L2	2	"6,566,734".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:31
L3	0	2003/0186511	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:31
L4	0	"210" and l3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L5	773780	"210" or l3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L6	5793	hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L7	1160	5 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L8	2	"5494697".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L9	2	"5767018".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L10	2	"6156629".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32

L11	6	L8 or L9 or L10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
L12	6	L11 or I3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:33
L13	1	12 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:34
L14	2	"6027975".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:48
L15	2	"6027975".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:48
L19	1583293	"32" and "33"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:55
L20	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55
L21	7830880	in	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55
L22	1562306	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55
L23	0	L20 adj L21 adj L22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:55

L24	0	L22 and L23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:56
L25	41	"5252881"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:57
L26	2	"5252881".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:57
L27	2	"6077755".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:58
L28	618	pad adj oxide same RIE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:58
L29	136207	HF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:58
L30	26536	NH3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:59
L31	3	28 and 30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:59
L32	3	31 and 29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 16:59
L33	6	etch near oxide same (NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH.subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:06

L34	5	33 and (HF or hydrofluric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:05
L35	5432	RIE and (HF or hydrofluric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:06
L36	67	35 and (NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH.subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:10
L37	1	34 and (pad adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:07
L38	58	HF near (NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH.subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 17:10
L39	3	38 and (pad adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:14
L40	0	High near plasma near oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:15
L41	2	High near plasma same oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:15
L42	7	HDP same oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:16
L43	0	42 and nitrid near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:17

L44	0	42 and nitride near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:17
L45	0	39 and ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:18
L46	0	42 and ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:18
L47	0	silicon adj Nitride near thichness near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:19
L48	223	silicon adj Nitride near thickness near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:19
L49	44	48 and MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:19
L50	13	49 and stop	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:20
L51	0	50 and CAdkissonD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:22
L52	13	50 and Cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:43
L53	7	hdp same oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:53

L54	1269	polysilicon and plasma same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L55	315	polysilicon and plasma near etch same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L56	20	55 and KOH	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L57	148	polysilicon same plasma near etch same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 18:54
L58	11	57 and KOH	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 19:04
L59	2	"5360995".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 19:15
L60	2	"5620922".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 19:22
L61	306	remove hard adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:23
L62	335	implant near polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:25
L63	0	61 and 62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:23

L64	227	polysilicon near gate near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:25
L65	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:25
L66	2	65 near 64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:32
L67	0	source near extensions near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:32
L68	10	(source or s/d) same extensions near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:32
S2	2	"6064092".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:54
S3	1	"20050170570"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:38
S4	1911895	oxide or oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S5	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:37
S6	1292034	concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:37

S7	89878	dopant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S8	1719	S4 near S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S9	1457	S4 near S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S10	36	S8 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S11	29	S10 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:38
S12	798306	oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S13	395	S12 neaR S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S14	929	S12 NEAR S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:41
S15	18	S13 AND S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:50
S16	486	S5 ADJ S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:51

S19	18347	locos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:52
S20	41	S16 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 08:52
S21	1	10/725848	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:11
S22	185175	ultra	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S23	1490498	thin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S24	1562306	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S25	46	S22 adj S23 adj S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:05
S26	28005	SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:06
S27	55525	S25 ans S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:06
S28	38	S25 and S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:17
S29	11	("6420218").URPN.	USPAT	OR	ON	2005/09/15 09:10

S30	142419	implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:17
S31	7830880	in	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:17
S32	1562306	channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:18
S34	1294	S32 adj S30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:19
S36	508	oxygen adj implant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:19
S40	3489	SIMOx	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:38
S41	84289	mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:21
S42	1290	S40 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22
S43	1332	thin adj channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:31
S44	28005	SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22

S45	78463	low adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22
S46	5811	low adj capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:22
S47	31	S42 and S43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:23
S48	31	S47 and S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:23
S49	5	S48 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:30
S50	2	S49 and S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:23
S52	46	ultra adj thin adj channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:32
S53	20	S52 and S40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:37
S54	1684	SIMO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:38
S55	157	SIMOx.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:39

S56	0	S55 and (channel near implant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:39
S57	18	S55 and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:40
S58	67146	anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:40
S59	47	S55 and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:06
S60	1040	thin$3 near SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S61	223	ultra adj thin$3 near SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S62	4	S59 and S60	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S63	0	S59 and S61	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:41
S64	2	"6420218".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 09:54

S65	40	("4683645" | "4745082" | "4784718" | "5017504" | "5264382" | "5270232" | "5349228" | "5374575" | "5391510" | "5393685" | "5429956" | "5434093" | "5478776" | "5538913" | "5576227" | "5593907" | "5607884" | "5668397" | "5675159" | "5716861" | "5726081" | "5736435" | "5793090" | "5801075" | "5811323" | "5814544" | "5817558" | "5824586" | "5825066" | "5856225" | "5858843" | "5904530" | "5915180" | "5915182" | "5915183" | "5937297" | "5953602" | "5972754" | "5998288" | "6190952").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/15 09:59
S71	136935	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S72	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S73	28005	SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S74	10	burried near oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S75	2038044	substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S76	676	S71 and S72 and S73 and74 and S75	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07
S77	3489	simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 10:07

S78	219	S76 and S77	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:11
S79	104	257/243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:09
S80	1	S79 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:10
S81	1	SIMO.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 11:11
S82	157	SIMOx.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:09
S83	2	"6417078".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:49
S84	9757	soi adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:50
S85	978	dielectric adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:49
S88	87	soi near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:53
S89	283	soi near channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:54

S90	5261	soi same channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 12:53
S91	98	S89 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:01
S92	2	"6417078".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:15
S93	84289	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:15
S96	1290	S93 and SIMOx	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S98	12383	hard adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S99	491787	dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S100	353	S98 near S99	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:16
S101	8	S96 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:21
S102	235	simox same mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:38

S10 3	0	simox adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:21
S10 4	1	09/955375	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:23
S10 5	0	"6551898.pn",	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:39
S10 6	2	"6551898".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:51
S10 7	2	"20040241916"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:51
S10 8	198	ibis.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:56
S10 9	25	S108 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:52
S11 0	769242	mitsubishi.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:56
S11 1	200	S110 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 13:57
S11 2	122	S111 and mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 14:03

S11 3	0	S111 and (dielectric near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 14:03
S11 4	59	simox and (dielectric near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 15:31
S11 5	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:03
S11 6	3489	simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:12
S11 7	136935	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:12
S11 8	225	S115 and S116 and S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:57
S11 9	3809	S115 same S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 16:57
S12 0	3	S119 same S116	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:02
S12 1	5049	S115 and S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:03
S12 3	545	channel adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:04

S12 5	3	S123 same S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:05
S12 6	486	implant adj oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:12
S12 9	2	"20020102813"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:09
S13 0	30	S126 and S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 1	77366	dummy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 2	964798	gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 3	1880164	region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 4	180	S131 near S132 near S133	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 17:42
S13 5	16	S134 and simox	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:01
S13 6	2586656	gate region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:01

S137	17963	gate adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S138	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S139	5793	HDP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S140	114444	polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:02
S141	413620	resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S142	199	oxygen adj ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:23
S143	156502	photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S144	15560	thermal adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S145	114444	polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:19
S146	44	(poly near etch) same HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:22

S148	1411	(Silicon adj Nitride) near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:20
S149	1550701	selective or selectivity or selectively	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:21
S150	13626	(pad adj oxide) nead HDP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:21
S151	0	.hF near NH3 near pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:21
S152	17	(hF near NH3) and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:22
S157	120	S148 and S149 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:24
S158	143	S142 and S143 and S143	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:24
S159	7538	S144 and S145	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:25
S160	0	S157 and S158 and S159	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:25
S161	10	S158 and S159	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:25

S16 2	2	S161 and S150	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:26
S16 3	0	S161 and S148	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:26
S16 4	435	forming adj dummy adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:27
S16 5	251	dummy adj gate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 18:29
S16 6	88	S165 and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:35
S16 7	1550	form near gate near structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:36
S16 8	84289	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:36
S16 9	532	S167 and S168	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:37
S17 0	142163	cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:37
S17 1	5793	hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:37

S17 2	9	S169 and S170 and S171	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 07:38
S17 3	61549	International adj Business adj machines	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S17 4	80176	"169" and "173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S17 5	1007	S174 and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:12
S17 6	22	S175 and hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:13
S17 7	22	S176 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:15
S17 8	2084	dummy adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:15
S17 9	30	"173" and S178	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:18
S18 0	0	S179 and (pad adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:19
S18 1	8652	pad adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:19

S18 2	163	S181 and S178	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:23
S18 3	0	S182 and "173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:19
S18 4	2	09/809211	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:54
S18 5	519	silicon adj oxide adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:55
S18 6	1	S185 near hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:56
S18 7	1	S185 same hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:55
S18 8	127337	silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:55
S18 9	120	S188 near hdp	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 09:59
S19 0	21	nitride near cvd near pecvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06
S19 1	21	S190 and nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06

S19 3	141789	((silicon adj nitride) or (SiN4 or SiNn or "SiN.sub4" or "SiN.subx" or "SiN. subn" or "SiN.sub.4" or "SiN.sub.x" or "SiN.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:06
S19 4	22	S193 near cvd near pecvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:09
S19 5	1449	S193 near cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:07
S19 6	1762	S193 near (nm or angstroms)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:10
S19 7	3	S196 near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:09
S19 8	1236	S193 near nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:10
S19 9	233	S198 same mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:17
S20 0	6801	etch$3 near under	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:19
S20 1	65	etch$3 near under near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:38
S20 2	9	etch near polysilicon near HBr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:54

S20 3	0	remove near resist near oxygen near ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:42
S20 4	3	remove near resist near ash same (oxygen or O2 or Ox or On or Osubx or Osubn or "O.subx" or "O.subn" or "O.sub.x" or "O.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:43
S20 5	567	remove near resist same (oxygen or O2 or Ox or On or Osubx or Osubn or "O.subx" or "O.subn" or "O.sub.x" or "O.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:45
S20 6	2	"5494697".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S20 7	2	"5767018".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S20 8	2	"6156629".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S20 9	0	S206 and S207 and S208	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S21 0	6	S206 or S207 or S208	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 16:32
S21 1	2	S210 and selectivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:47
S21 2	8	S202 and (selectivity or selective or selectively)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:55

S21 3	0	KOH near polysilicon near (selectivity or selective or selectively)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:55
S21 4	2	KOH near polysilicon near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:56
S21 5	9	KOH near polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:59
S21 6	2	"6566734"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:28
S21 7	395	polysilicon near (thermal adj oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:10
S21 8	15	S217 near gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:11
S21 9	2025025	nitride selective to oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:14
S22 0	9	etch adj nitride near selective near oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:16
S22 1	43	etch adj nitride near selective	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:18
S22 2	1443483	oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:16

S22 3	9	S221 near S222	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:16
S22 4	0	pad adj oxide near etch near (NF and NH3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:19
S22 5	0	pad adj oxide near etch near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 6	0	pad adj oxide near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 7	0	etch adj oxide near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 8	1	etch near oxide near (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:20
S22 9	11	etch near oxide same (NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF.subNF" or "NF.sub.x" or "NF.sub.NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 11:25
S23 2	1145	doped polysilicon gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:28
S23 3	2440	remove mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 19:22
S23 7	57	implant near source/drain near ((IIIA and v) or (n+ and p+))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:34

S23 9	1617	source/drain adj extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:47
S24 3	1948221	thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:37
S24 4	11	S239 near S243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:37
S24 9	1139	extension near thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:41
S25 0	1	S249 near (s/d or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:42
S25 1	1688	(source/drain or s/d) adj extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:48
S25 2	11	S251 near S243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 11:48
S25 3	337	S251 same S243	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 13:10
S25 4	57	Si near SiGe near SiGeC near SiC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/09/16 13:11
S25 5	4	etch near oxide same ((NH3 or NHx or NHNH or NHsubx or NHsubNH or "NH. subx" or "NH.subNH" or "NH.sub.x" or "NH.sub.NH") and HF)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 13:45